

JC12 Rec'd PCT/PTC 19 OCT 2005

SHEET 1 OF 1

| | | | | | |
|--|--|--|--|---|--|
| INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449) | | ATTY. DOCKET NO. 071971-0388 | | SERIAL NO. Not yet assigned 10/553628 | |
| | | APPLICANT Masao UCHIDA, et al. | | | |
| | | FILING DATE October 19, 2005 | | GROUP 2814 Not yet assigned | |

| U.S. PATENT DOCUMENTS | | | | | |
|-----------------------|----------|---|--------------------------------|---|---|
| EXAMINER'S INITIALS | CITE NO. | Document Number Number-Kind Code(s) of country | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
| Mbh | | US 2003/0080384 A1 | 5/20/03 | Takahashi et al. | Corresponds to JP 2003-234301 A |
| Mbh | | US 5977564 A | 11/19/99 | Kobayashi et al. | Corresponds to JP 10-321854 A |
| Mbh | | US 6097039 A | 8/20/00 | Peters et al. | Corresponds to JP 2001-617375 A |
| | | | | | |
| | | | | | |
| | | | | | |
| | | | | | |
| | | | | | |
| | | | | | |

| FOREIGN PATENT DOCUMENTS | | | | | | | |
|--------------------------|----------|--|--------------------------------|---|---|-------------|----------------------------|
| EXAMINER'S INITIALS | CITE NO. | Foreign Patent Document Country Code-Number-Kind Code(s) (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines Where Relevant Figures Appear | Translation | |
| | | | | | | Yes | No |
| Mbh | | JP 2003-234301 A | 08-22-2003 | Matsushita Electric Industrial Co., Ltd. | Corresponds to US 2003/0080384 A1 | | |
| Mbh | | JP 2003-209251 A | 07-25-03 | Japan Atomic Energy Research Institute | | | |
| Mbh | | JP 10-321854 A | 12-04-1998 | Toshiba Corp. | Corresponds to US 5977564 A | | |
| Mbh | | JP 2000-294777 A | 10-20-2000 | Mitsubishi Electric Corp. | | | |
| Mbh | | JP 2001-617375 A | 10-02-2001 | Siemens AG. | Corresponds to US 6097039 A | | |
| Mbh | | JP 2001-144288 A | 06-25-2001 | Denso Corp. | | | |
| Mbh | | JP 2002-280381 A | 09-27-2002 | Fuji Electric Co., Ltd. | | | |
| Mbh | | WO 98/48163 | 09-23-1999 | HITACHI LTD. | | | JAPAN (w/English Abstract) |

| OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) | | |
|--|----------|---|
| EXAMINER'S INITIALS | CITE NO. | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. |
| Mbh | | G.Y. CHUNG, et al., "Improved Invention Channel Mobility for 4H-SiC MOSFETs Following High Temperature Anneals in Nitric Oxide," Electron Device Letters, April 2001, pp 176-178, Vol 22, No. 4, IEEE |
| | | |
| | | |
| | | |

| | |
|-------------------------------------|--------------------------------------|
| EXAMINER /Mursalin Hafiz/ | DATE CONSIDERED 02/16/2007 |
|-------------------------------------|--------------------------------------|

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
 1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.